

00000000000000000000000000000000

2. A method according to claim 1, wherein the modifying of the critical regions is undertaken so that no under-etching can be formed, said modified critical regions being integrated into the existing data structure of the layout.

4. A method according to claim 1, wherein the critical region is adjustable by an admissible, fabrication-oriented, minimal spacing between the configuration elements.

5. A method according to claim 4, wherein the critical regions between the configuration elements are filled out by polygons so that the critical regions between the configuration elements are avoided.

6. A method according to claim 5, wherein the polygons of the critical regions are limited given possible superimpositions of the configuration elements.

7. A method according to claim 6, wherein the polygons of the critical regions are enlarged slightly so that the edges of the polygons superimpose with the edges of the configuration elements.